



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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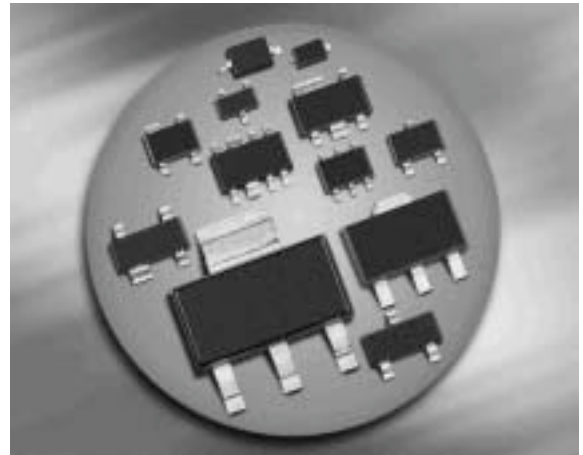
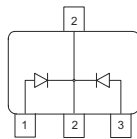
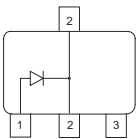
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Silicon Switching Diodes

- Switching applications
- High breakdown voltage
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101


BAW78D
BAW79D


Type	Package	Configuration	Marking
BAW78D	SOT89	single	GD
BAW79D	SOT89	common cathode	GH

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	400	V
Peak reverse voltage	V_{RM}	400	
Forward current	I_F	1	A
Peak forward current	I_{FM}	1	
Peak forward current	I_{FM}	1	
Surge forward current, $t = 1 \mu\text{s}$	I_{FS}	10	
Non-repetitive peak surge forward current	I_{FSM}	-	
Total power dissipation	P_{tot}		W
BAW78D, $T_S \leq 125^\circ\text{C}$		1	
BAW79D, $T_S \leq 115^\circ\text{C}$		1	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

¹⁾Pb-containing package may be available upon special request

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BAW78D		≤ 25	
BAW79D		≤ 35	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

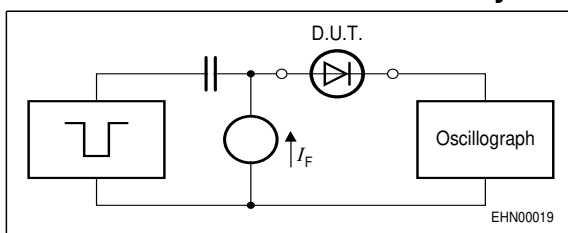
Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Breakdown voltage $I_{(BR)} = 100 \mu\text{A}$	$V_{(BR)}$	400	-	-	V
Reverse current $V_R = 400 \text{ V}$ $V_R = 400 \text{ V}, T_A = 150 \text{ }^\circ\text{C}$	I_R	-	-	1 50	μA
Forward voltage $I_F = 1 \text{ A}$ $I_F = 2 \text{ A}$	V_F	-	-	1.6 2	V

AC Characteristics

Diode capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	-	10	-	pF
Reverse recovery time $I_F = 200\text{mA}, I_R = 200\text{mA}$, measured at $I_R = 20\text{mA}$ $R_L = 100\Omega$	t_{rr}	-	1	-	μs

Test circuit for reverse recovery time


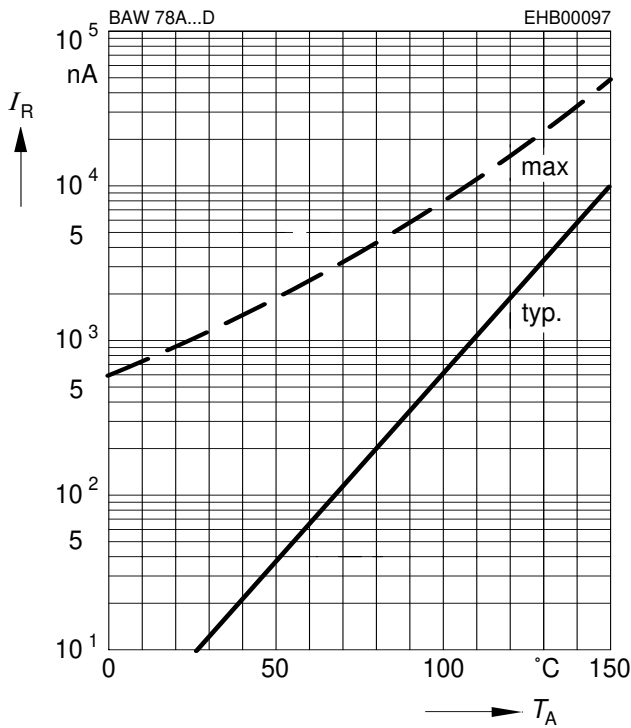
Puls generator: $t_p = 10\mu\text{s}$, $D = 0.05$,
 $t_r = 0.6\text{ns}$, $R_i = 50\Omega$

Oscilloscop: $R = 50\Omega$, $t_r = 0.35\text{ns}$
 $C \leq 1\text{pF}$

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

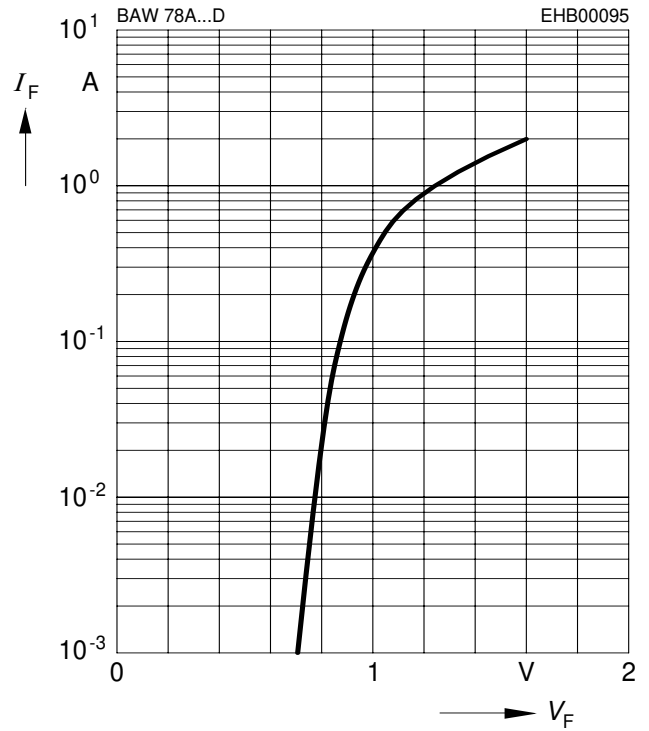
Reverse current $I_R = f(T_A)$

$V_R = 400V$

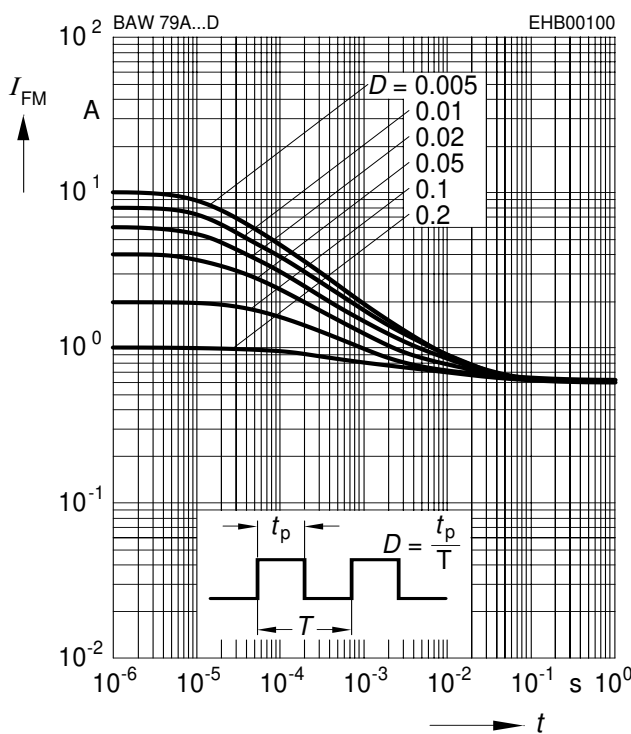


Forward current $I_F = f(V_F)$

$T_A = 25^\circ C$

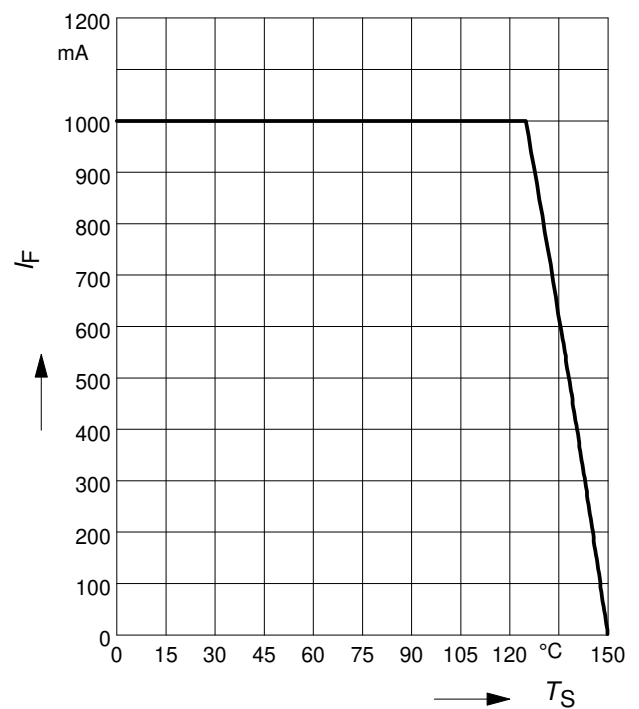


Peak forward current $I_{FM} = f(t_p)$



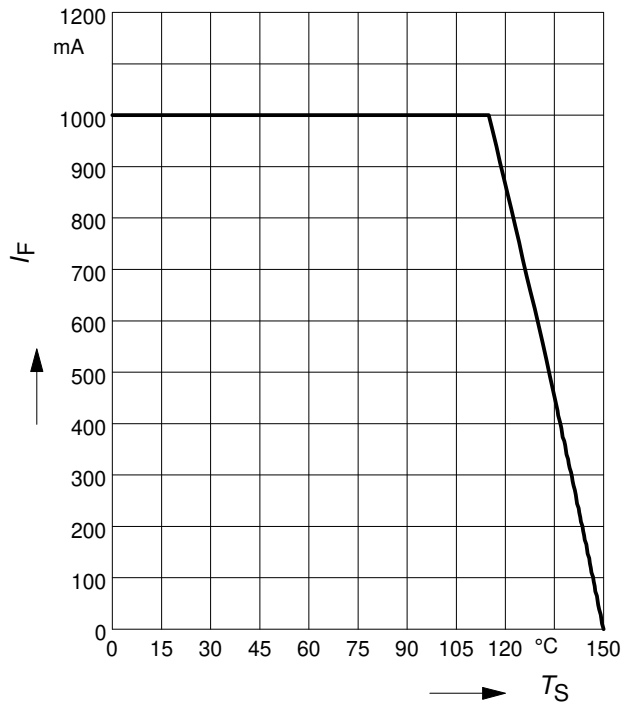
Forward current $I_F = f(T_S)$

BAW78D

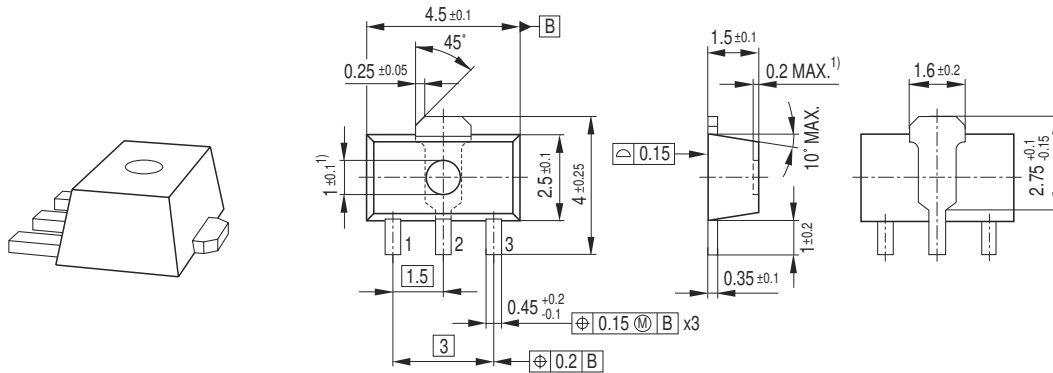


Forward current $I_F = f(T_S)$

BAW79D

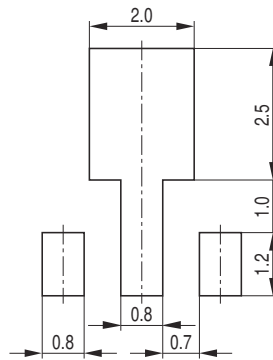


Package Outline

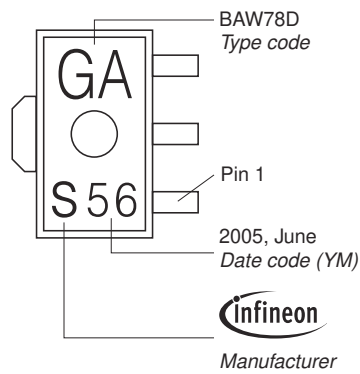


1) Ejector pin markings possible

Foot Print

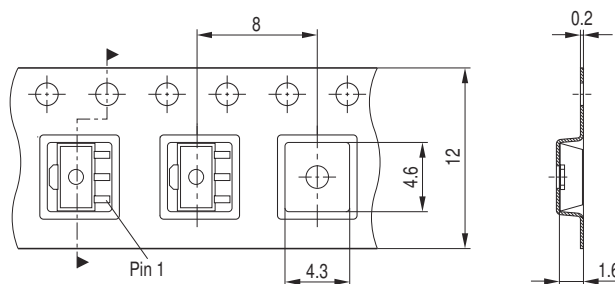


Marking Layout (Example)



Standard Packing

Reel $\phi 180 \text{ mm} = 1.000 \text{ Pieces/Reel}$
 Reel $\phi 330 \text{ mm} = 4.000 \text{ Pieces/Reel}$



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